# NSN 5961-01-465-5108

Diode Semiconductor Device - Page 1 of 1

View Online at https://aerobasegroup.com/nsn/5961-01-465-5108

**Inclosure Material:**

Glass

**End Application:**

6625-01-391-2969

**Mounting Facility Quantity:**

2

**Mounting Method:**

Press fit

**Semiconductor Material:**

Silicon

**Voltage Rating In Volts Per Characteristic:**

56.0  forward gate to source breakdown voltage and 1.8  forward gate to source breakdown voltage

**Current Rating Per Characteristic:**

1.50 nanoamperes forward current,  average peak

**Power Rating Per Characteristic:**

500.0 milliwatts small-signal output power,  common-base preset

**Maximum Operating Tempurature Per Measurement Point:**

-65.0 degrees celsius case and 200.0 degrees celsius case

**Special Features:**

Hermeticallysealed

**Terminal Type And Quantity:**

2 case

**Shelf Life:**

N/a

**Unit Of Measure:**

--

**Demilitarization:**

No

**Fiig:**

A110a0